

2SC495 2SC496

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

MEDIUM POWER AMPLIFIER APPLICATIONS.

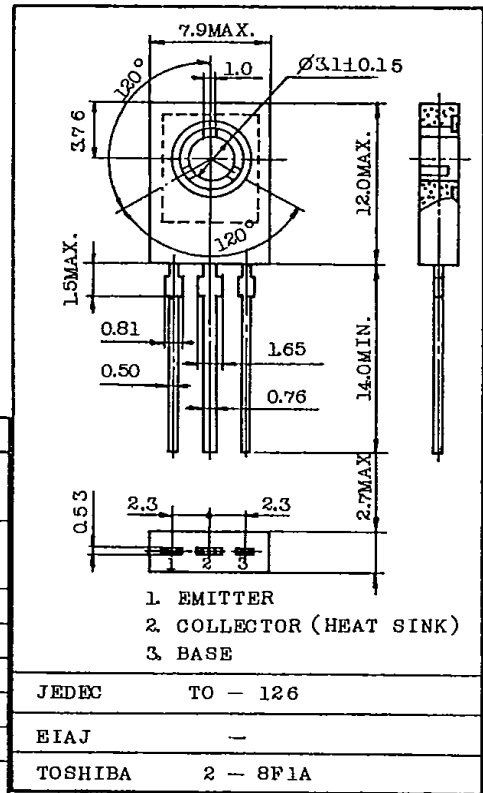
FEATURES:

- Low Collector Saturation Voltage
: $V_{CE(sat)}=0.25V$ (Typ.)
- 0.5 ~ 2 Watts Output Application.
- Complementary to 2SA505 and 2SA496.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	VCBO	2SC495	70	V
		2SC496	40	
Collector-Emitter Voltage	VCEO	2SC495	50	V
		2SC496	30	
Emitter-Base Voltage	VEBO	5	V	
Collector Current	IC	1	A	
Emitter Current	IE	-1	A	
Collector Power Dissipation	PC	1	W	
Junction Temperature	Tj	150	°C	
Storage Temperature Range	Tstg	-55 ~ 150	°C	

Unit in mm



Mounting Kit No. AC46C
Weight : 0.72g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	ICBO	VCB=30V, IE=0	-	-	1.0	µA	
Emitter Cut-off Current	IEBO	VEB=5V, IC=0	-	-	1.0	µA	
Collector-Emitter Breakdown Voltage	V(BR)CEO	IC=10mA, IB=0	2SC495	50	-	-	V
			2SC496	30	-	-	
Emitter-Base Breakdown Voltage	V(BR)EBO	IE=1mA, IC=0	5	-	-	V	
DC Current Gain	hFE(1) (Note)	VCE=2V, IC=50mA	40	-	240		
	hFE(2)	VCE=2V, IC=800mA	13	-	-		
Collector-Emitter Saturation Voltage	VCE(sat)	IC=500mA, IB=50mA	-	0.25	0.8	V	
Base-Emitter Voltage	VBE	VCE=2V, IC=500mA	-	0.9	1.1	V	
Transition Frequency	fT	VCE=10V, IC=10mA	50	100	-	MHz	
Collector Output Capacitance	Cob	VCB=10V, IE=0, f=1MHz	-	10	-	pF	

Note : hFE(1) Classification R : 40~80, O : 70~140, Y : 120~240

